NSN 5961-01-013-0080

Transistor - Page 1 of 1

Fiig: A110a0



View Online at https://aerobasegroup.com/nsn/5961-01-013-0080 **Inclosure Material:** Metal **Overall Length:** 0.340 inches **Overall Diameter:** 0.500 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 120.0 breakdown voltage, collector-to-base, emitter open and 75.0 collector to emitter reverse voltage and 7.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** Between 2.00 amperes source cutoff current and 4.00 amperes source cutoff current **Power Rating Per Characteristic:** 35.0 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 2 uninsulated wire lead and 1 case Shelf Life: N/a **Unit Of Measure: Demilitarization:** No